



ASX RELEASE

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4DS DEMONSTRATES CELL SCALABILITY TO 50NM, ESSENTIAL FOR HIGH DENSITY GIGABYTE STORAGE

- 4DS has developed a scalable non-filamentary ReRAM memory cell at a 50 nanometre (**nm**) lithography, a breakthrough in ReRAM technology
- 50nm represents significant progress towards the development of next generation mobile and cloud silicon storage
- The next goal is to demonstrate viable scalability below 50nm
- Updates will be provided as 4DS approaches scalability required for high density silicon storage
- Investor roadshows will occur in Australia and the US

4DS Memory Limited (ASX:4DS) (**4DS**) today announced the successful development of a scalable non-filamentary resistive random access memory (**ReRAM**) cell at a 50 nanometre (**nm**) lithography, a geometry required for high density gigabyte storage required in mobile devices and the cloud.

Chief Executive Officer and Managing Director, Dr Guido Arnout, said “The development of our ReRAM technology has made significant progress in demonstrating the scalability required for high density storage.

“50 nanometres represents an essential step towards viable gigabyte silicon storage.

“4DS is the first company to achieve a non-filament ReRAM cell in a 50 nanometre lithography. The significance is that this parallels the geometries of 3D Flash memory today.”

NAND Flash (**Flash**) is an estimated annual US\$40 billion market.

The increasing need for fast and economical storage solutions across diverse applications will further drive market growth over the next five years. However, Flash has a diminishing ability to scale further and meet the future need for more storage in less physical space.

Of all the emerging memory storage technologies in development, ReRAM-based disruptive technologies have been identified by major semiconductor corporations and industry analysts as the best potential replacement for Flash.

What sets the 4DS memory cell apart is the filament-less switching mechanism, the best solution for high density non-volatile memory for mobile and cloud, representing a breakthrough in ReRAM technology.

Development is progressing in accordance with the scope of work defined in the joint development agreement with HGST, a leading global storage provider. The next goal is to demonstrate viable scalability below 50nm.

The strength of 4DS' proprietary technology and materials deposition process is anchored by 15 US patents.

4DS will provide updates as improvements continue towards the smallest cell geometries that can be reliably fabricated.

4DS has released an updated presentation to coincide with an Australian investor roadshow.



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4DS Memory Limited (ASX:4DS), with research and development facilities located in Silicon Valley, is a developer of non-volatile memory technology, pioneering non-filamentary ReRAM for next generation storage in mobile and cloud. Established in 2007, 4DS owns a patented IP portfolio developed in house to create high density gigabyte storage.

For further information, visit www.4dsmemory.com or contact Mel Buffier at mel.buffier@4dsmemory.com or +61 411 622 899.

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